



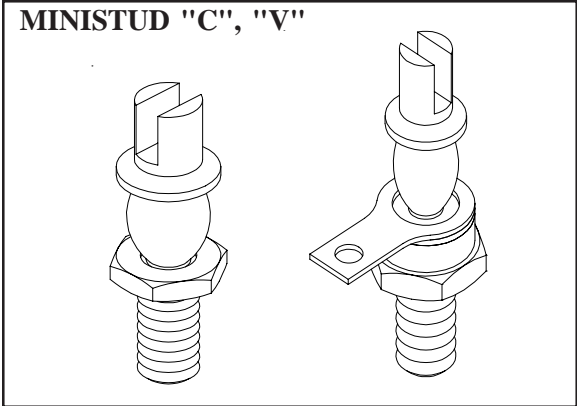
SOLID STATE DEVICES, INC.

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 ssdi@ssdi-power.com * www.ssdi-power.com

Designer's Data Sheet

**S6189F6
 thru
 S6189F10**

**9 AMP
 600 - 1000 VOLTS
 FAST RECOVERY
 RECTIFIER**



- FEATURES:**
- 90097 types where higher voltages are needed
 - Fast Recovery: 250 ns
 - PIV to 1000 Volts
 - Low Reverse Leakage Current
 - Hermetically Sealed Ministud Packages
 - Single Chip Construction
 - High Surge Rating
 - Low Thermal Resistance
 - TX, TXV, and Space Level Screening Available
 - Available in Ultrafast or Hyperfast Versions

Maximum Ratings		SYMBOL	VALUE	UNITS
Peak Repetitive Reverse and DC Blocking Voltage	S6189F6C , V S6189F8C , V S6189F10C , V	V_{RRM} V_{RWM} V_R	600 800 1000	Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, $T_A = 25^\circ\text{C}$)		I_o	9	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave , $T_A = 25^\circ\text{C}$)		I_{FSM}	150	Amps
Operating Temperature Range		T_{OP}	-65 TO +175	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-65 TO +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	"V" Isolated "C" Hot Case	$R_{\theta JL}$	7.5 4.0	$^\circ\text{C/W}$

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: R000170 Sheet4U.com

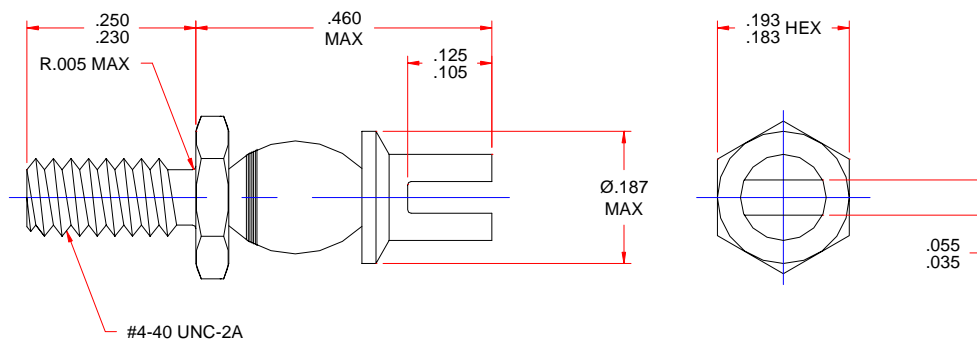
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Electrical Characteristics	SYMBOL	MAX	UNITS
Instantaneous Forward Voltage Drop ($I_F = 9A_{dc}$, $T_A = 25^\circ C$, 300 μs Pulse)	V_F	1.2	V _{dc}
Instantaneous Forward Voltage Drop ($I_F = 9A$, $T_A = -55^\circ C$, 300 μs Pulse)	V_F	1.3	V _{dc}
Reverse Leakage Current (Rated V_R , $T_A = 25^\circ C$, 300 μs min Pulse)	I_R	10	μA
Reverse Leakage Current (Rated V_R , $T_A = 100^\circ C$, 300 μs min Pulse)	I_R	50	μA
Junction Capacitance ($V_R = 10 V_{dc}$, $T_A = 25^\circ C$, $f = 1 Mhz$)	C_j	50	pf
Reverse Recovery Time ($I_F = 500mA$, $I_R = 1A$, $I_{RR} = 250mA$, $T_A = 25^\circ C$)	t_{RR}	250	nsec

MINISTUD (C*)



MINISTUD (V*)

